

/ Descriptions

Silicon PNP transistor in a SOT-23 Plastic Package.

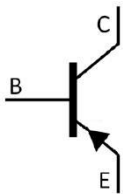
/ Features

Complementary pair with 2SD601A.

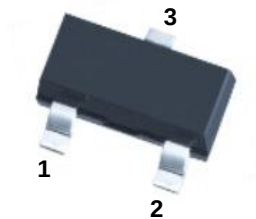
/ Applications

General power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	R	S
h_{FE} Range	160~260	210~340	290~460
Marking	H1BQ	H1BR	H1BS

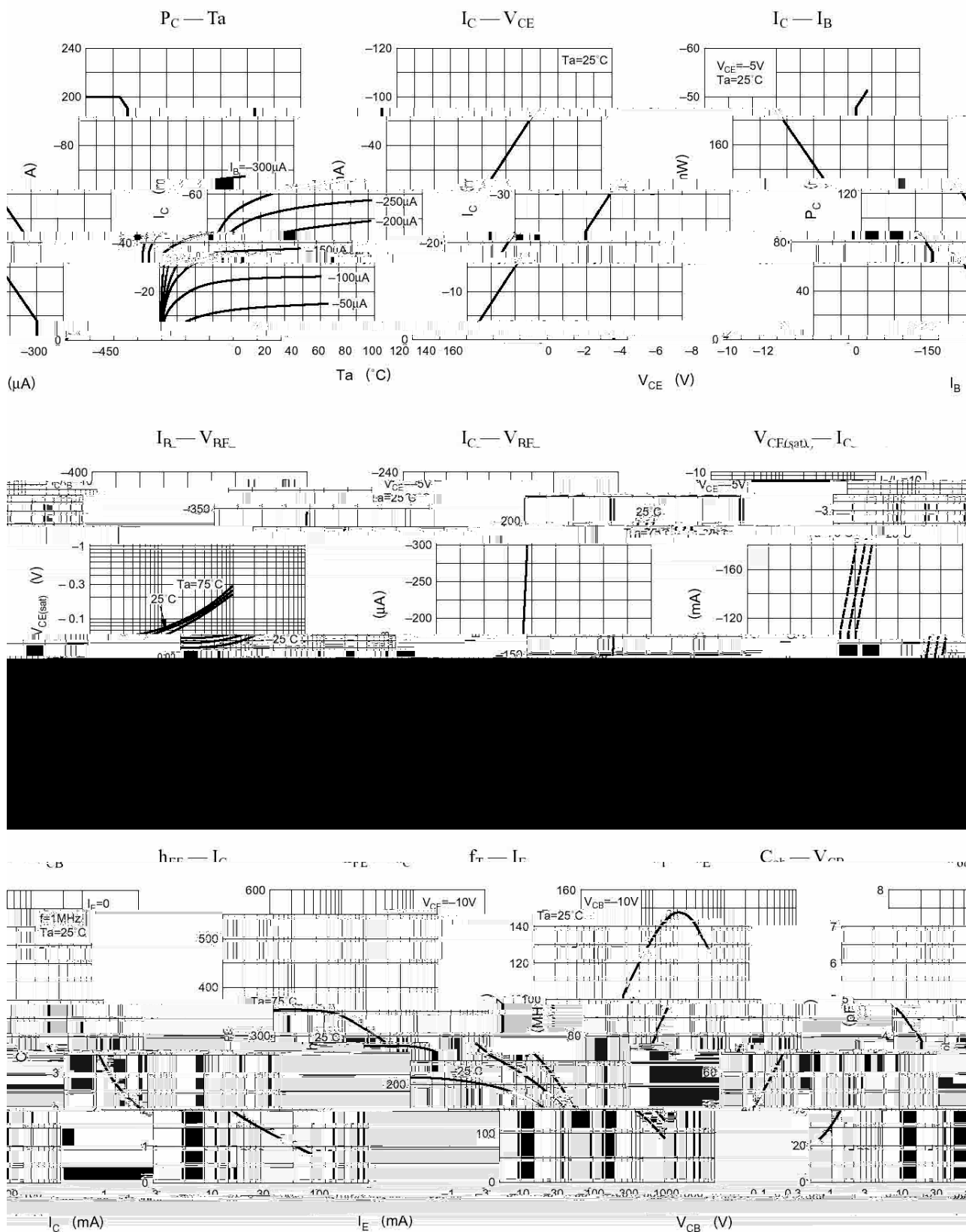
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-45	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current	I_C	-100	mA
Collector Current(pulse)	I_{CP}	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-45			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-2mA$ $I_B=0$	-45			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-7			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-20V$ $I_E=0$			-0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{CE}=-10V$ $I_B=0$			-100	μA
DC Current Gain	h_{FE}	$V_{CE}=-10V$ $I_C=-2mA$	160		460	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA$ $I_B=-10mA$		-0.3	-0.5	V
Transition Frequency	f_T	$V_{CB}=-10V$ $I_C=-1mA$ $f=200MHz$		80		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=1MHz$		2.7		pF

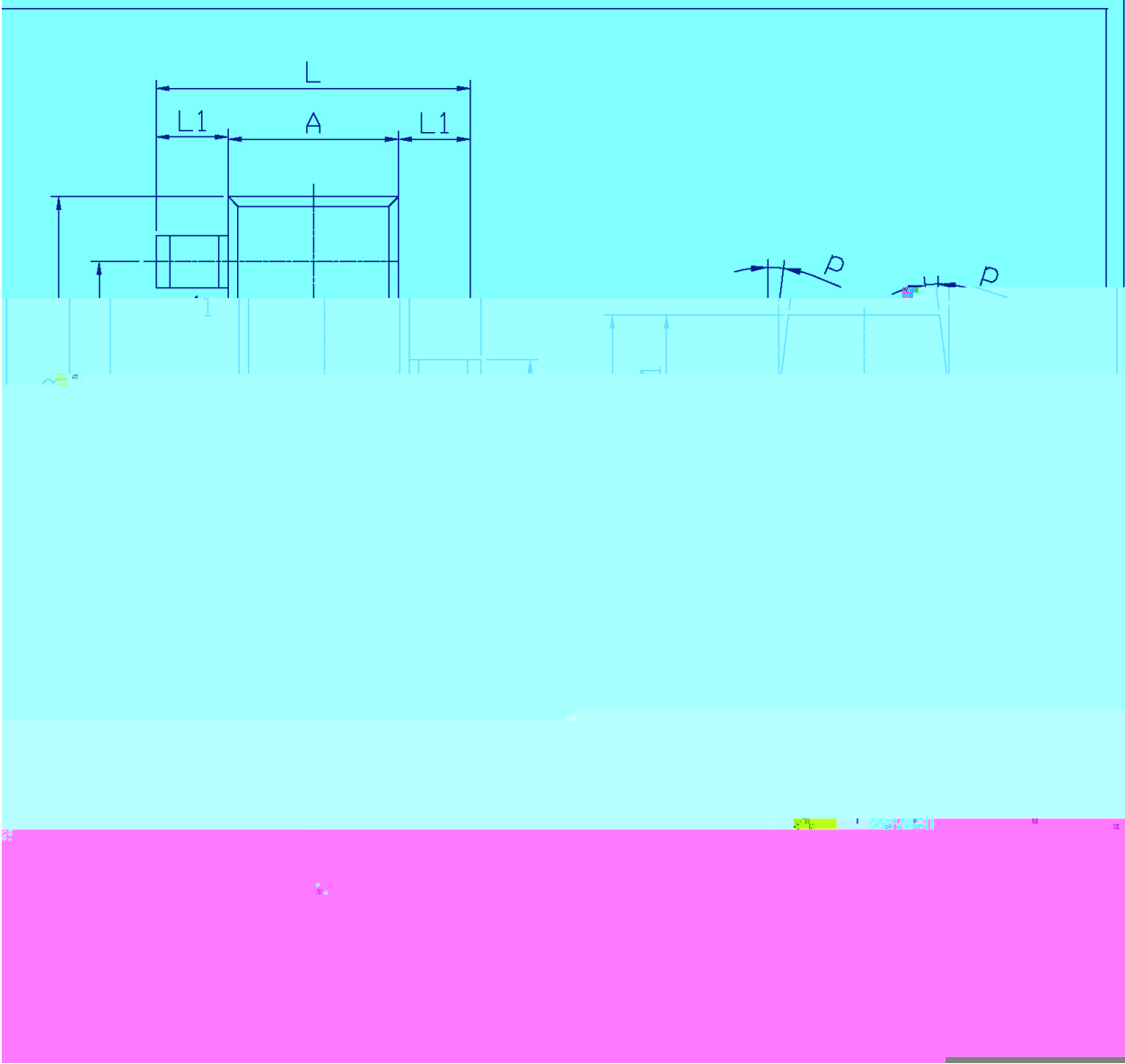
Electrical Characteristic Curve



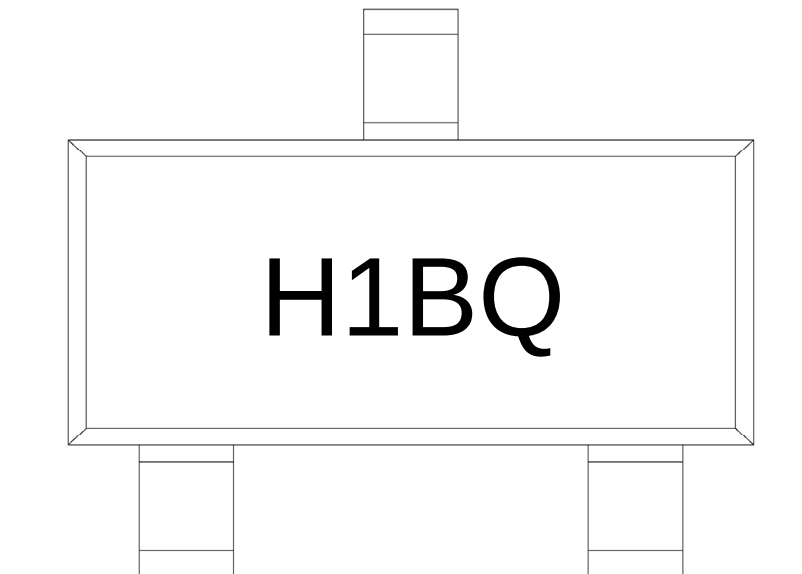
/ Package Dimensions

SOT-23

单位: mm



/ Marking Instructions



h_{FE}

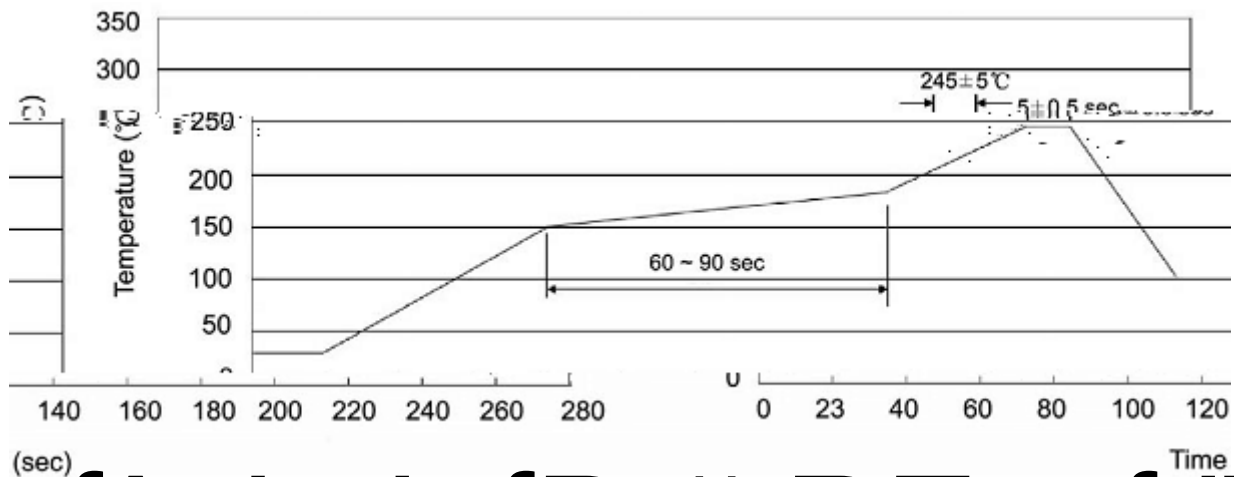
Note:

H: Company Code

1B: Product Type Code

Q: h_{FE} Classifications Symbol Code

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Note:

1. Preheating: 25~150 , Time: 60~90 sec.
2. Peak Temp.: 245 ± 5 , Duration: 5 ± 0.5 sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions